Darlington Complementary Silicon Power Transistors

- ... designed for general-purpose amplifier and low frequency switching applications.
- High DC Current Gain Min hFE = 1000 @ $I_C = 5 A$, $V_{CE} = 4 V$
- Collector–Emitter Sustaining Voltage @ 30 mA
 VCEO(sus) = 60 Vdc (Min) TIP140, TIP145
 80 Vdc (Min) TIP141, TIP146
 100 Vdc (Min) TIP142, TIP147
- · Monolithic Construction with Built-In Base-Emitter Shunt Resistor

MAXIMUM RATINGS

Rating	Symbol	TIP140 TIP145	TIP141 TIP146	TIP142 TIP147	Unit
Collector–Emitter Voltage	VCEO	60	80	100	Vdc
Collector-Base Voltage	VCB	60	80	100	Vdc
Emitter-Base Voltage	V _{EB}	5.0			Vdc
Collector Current — Continuous Peak (1)	lC	10 15			Adc
Base Current — Continuous	ΙΒ	0.5			Adc
Total Device Dissipation @ T _C = 25°C	PD	125			Watts
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150			°C

THERMAL CHARACTERISTICS

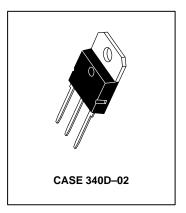
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.0	°C/W
Thermal Resistance, Case to Ambient	$R_{ heta JA}$	35.7	°C/W

(1) 5 ms, \leq 10% Duty Cycle.

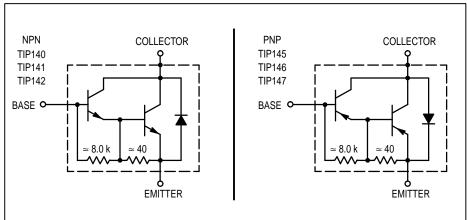
TIP140 TIP141* TIP142* PNP TIP145 TIP146* TIP147*

*Motorola Preferred Device

10 AMPERE
DARLINGTON
COMPLEMENTARY SILICON
POWER TRANSISTORS
60-100 VOLTS
125 WATTS



DARLINGTON SCHEMATICS



Preferred devices are Motorola recommended choices for future use and best overall value

REV 1



ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•	•		•
Collector–Emitter Sustaining Voltage (1) (I _C = 30 mA, I _B = 0)	TIP140, TIP145 TIP141, TIP146 TIP142, TIP147	VCEO(sus)	60 80 100	_ _ _	_ _ _	Vdc
Collector Cutoff Current (VCE = 30 Vdc, IB = 0) (VCE = 40 Vdc, IB = 0) (VCE = 50 Vdc, IB = 0)	TIP140, TIP145 TIP141, TIP146 TIP142, TIP147	ICEO	_ _ _	_ _ _ _	2.0 2.0 2.0	mA
Collector Cutoff Current (V _{CB} = 60 V, I _E = 0) (V _{CB} = 80 V, I _E = 0) (V _{CB} = 100 V, I _E = 0)	TIP140, TIP145 TIP141, TIP146 TIP142, TIP147	I _{CBO}	_ _ _	_ _ _	1.0 1.0 1.0	mA
Emitter Cutoff Current (V _{BE} = 5.0 V)		I _{EBO}	_	_	20	mA
ON CHARACTERISTICS (1)						
DC Current Gain (I _C = 5.0 A, V _{CE} = 4.0 V) (I _C = 10 A, V _{CE} = 4.0 V)		hFE	1000 500	_ _	_ _	_
Collector–Emitter Saturation Voltage (I _C = 5.0 A , I _B = 10 mA) (I _C = 10 A , I _B = 40 mA)		VCE(sat)	_	_	2.0 3.0	Vdc
Base–Emitter Saturation Voltage (I _C = 10 A, I _B = 40 mA)		V _{BE(sat)}	_	_	3.5	Vdc
Base–Emitter On Voltage (I _C = 10 A, V _{CE} = 4.0 Vdc)		V _{BE(on)}	_	_	3.0	Vdc
SWITCHING CHARACTERISTICS				•		•
Resistive Load (See Figure 1)						
Delay Time		t _d	_	0.15	_	μs
			_	0.55	_	μs
Storage Time $IB = 20 \text{ mA}$, Duty Cycle $\leq 2.0\%$, $IB_1 = IB_2$, RC & RB Varied, TJ = 25° C)		t _S	_	2.5	_	μs
Fall Time	7		_	2.5	_	μѕ

⁽¹⁾ Pulse Test: Pulse Width = $300 \mu s$, Duty Cycle $\leq 2.0\%$.

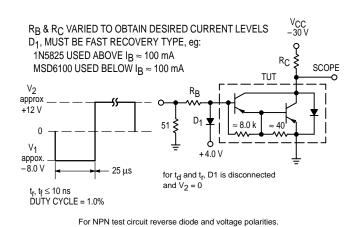


Figure 1. Switching Times Test Circuit

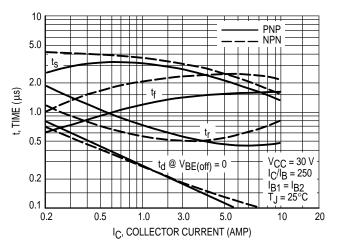


Figure 2. Switching Times

TYPICAL CHARACTERISTICS

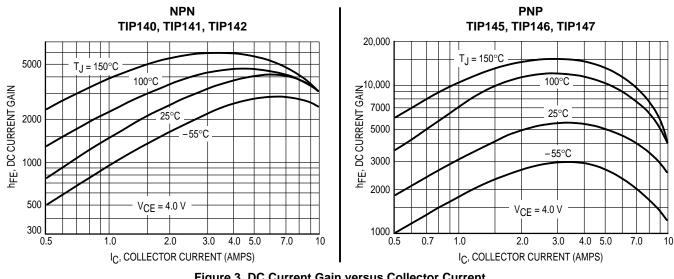


Figure 3. DC Current Gain versus Collector Current

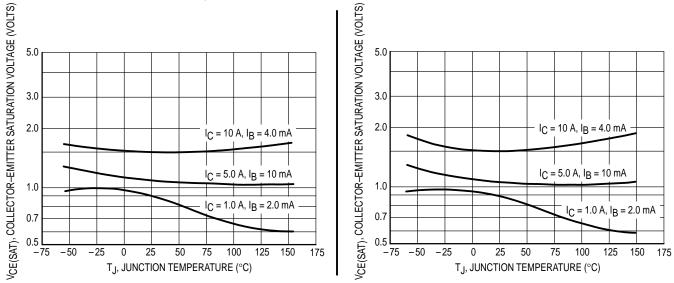


Figure 4. Collector-Emitter Saturation Voltage

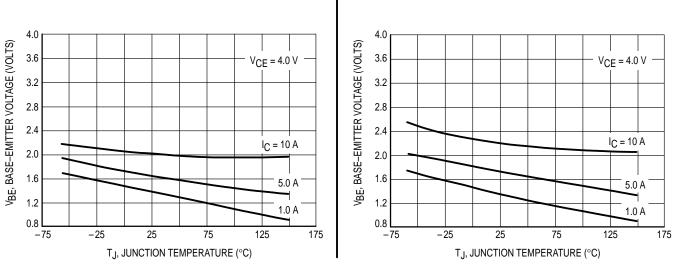
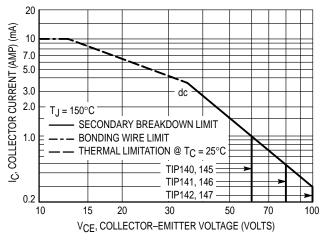


Figure 5. Base-Emitter Voltage

ACTIVE-REGION SAFE OPERATING AREA

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

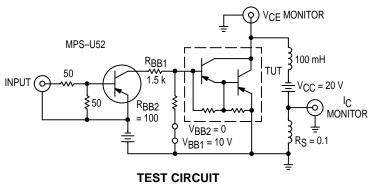
The data of Figure 6 is based on $T_{J(pk)} = 150^{\circ}C$; T_{C} is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

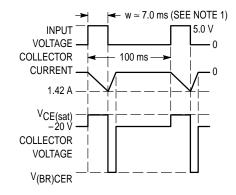


15 10 10 7.0 5.0 100 mJ 100 mJ

Figure 6. Active-Region Safe Operating Area

Figure 7. Unclamped Inductive Load

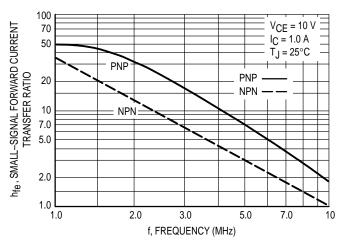




NOTE 1: Input pulse width is increased until I_{CM} = 1.42 A. NOTE 2: For NPN test circuit reverse polarities.

VOLTAGE AND CURRENT WAVEFORMS





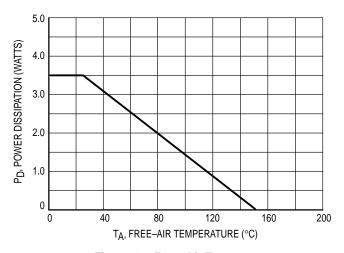
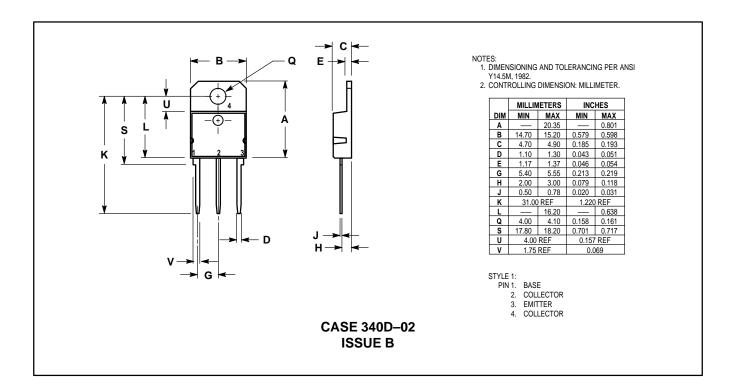


Figure 9. Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio

Figure 10. Free-Air Temperature Power Derating

PACKAGE DIMENSIONS



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TIP140/D